



STL65DN3LLH5

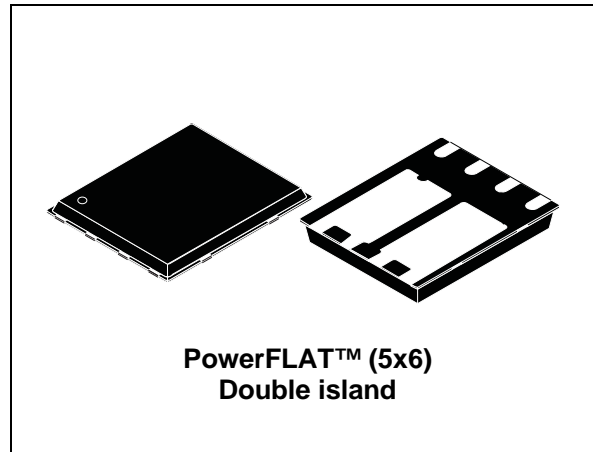
Dual N-channel 30 V, 0.0059 Ω , 19 A
PowerFLAT™(5x6) double island, STripFET™ V Power MOSFET

Features

Type	V _{DSS}	R _{DS(on) max}	I _D
STL65DN3LLH5	30 V	<0.0065 Ω	19 A ⁽¹⁾

1. The value is rated according R_{thj-pcb}

- R_{DS(on)} * Q_g industry benchmark
- Extremely low on-resistance R_{DS(on)}
- Very low switching gate charge
- High avalanche ruggedness
- Low gate drive power losses



Application

Switching applications

Description

This product utilizes the 5th generation of design rules of ST's proprietary STripFET™ technology. The lowest available R_{DS(on)}*Q_g, in this chip scale package, makes this device suitable for the most demanding DC-DC converter applications, where high power density is to be achieved.

Figure 1. Internal schematic diagram

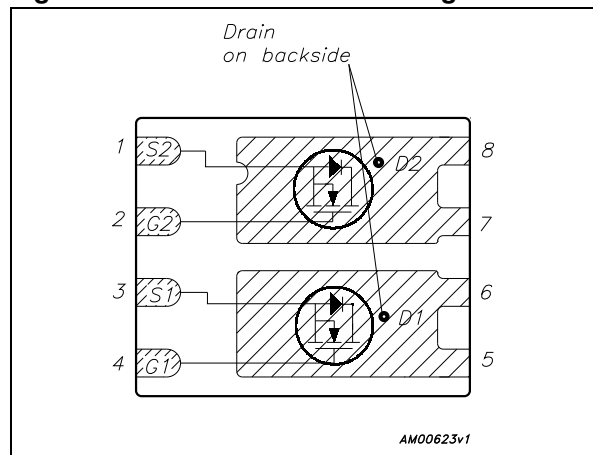


Table 1. Device summary

Order code	Marking	Package	Packaging
STL65DN3LLH5	65DN3LLH5	PowerFLAT™(5x6) Double island	Tape and reel

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	30	V
V_{GS}	Gate-source voltage	± 22	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	65	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100^\circ\text{C}$	41	A
$I_D^{(2)}$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	19	A
$I_D^{(2)}$	Drain current (continuous) at $T_C = 100^\circ\text{C}$	11.8	A
$I_{DM}^{(3)}$	Drain current (pulsed)	76	A
$P_{TOT}^{(1)}$	Total dissipation at $T_C = 25^\circ\text{C}$	60	W
$P_{TOT}^{(2)}$	Total dissipation at $T_C = 25^\circ\text{C}$	4	W
	Derating factor	0.03	W/ $^\circ\text{C}$
T_J	Operating junction temperature	-55 to 150	$^\circ\text{C}$
T_{stg}	Storage temperature		

1. The value is rated according R_{thj-c}
2. The value is rated according $R_{thj-pcb}$
3. Pulse width limited by safe operating area

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case (drain) (steady state)	2.08	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-ambient	32	$^\circ\text{C}/\text{W}$

1. When mounted on FR-4 board of 1inch², 2oz Cu, $t < 10$ sec

Table 4. Avalanche data

Symbol	Parameter	Value	Unit
I_{AV}	Not-repetitive avalanche current, (pulse width limited by T_J max)	18.5	A
E_{AS}	Single pulse avalanche energy (starting $T_J = 25^\circ\text{C}$, $I_D = I_{AV}$, $V_{DD} = 24$ V)	270	mJ

2 Electrical characteristics

($T_{CASE}=25^{\circ}C$ unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250 \mu A, V_{GS} = 0$	30			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating},$ $V_{DS} = \text{Max rating @ } 125^{\circ}C$			1 10	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 22 V$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1	1.5		V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10 V, I_D = 9.5 A$ $V_{GS} = 4.5 V, I_D = 9.5 A$		0.0059 0.0071	0.0065 0.0079	Ω Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25 V, f = 1 \text{ MHz},$ $V_{GS} = 0$	-	1500	-	pF
C_{oss}	Output capacitance			230		pF
C_{rss}	Reverse transfer capacitance			23		pF
Q_g	Total gate charge	$V_{DD} = 15 V, I_D = 19 A$	-	12	-	nC
Q_{gs}	Gate-source charge	$V_{GS} = 4.5 V$		5		nC
Q_{gd}	Gate-drain charge	(see Figure 14)		4.4		nC
R_G	Intrinsic gate resistance	$f = 1 \text{ MHz open drain},$ Bias=0 test signal level = 20 mV, open drain	-	1.6	-	Ω

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit	
$t_{d(on)}$	Turn-on delay time	$V_{DD}=15\text{ V}$, $I_D=9.5\text{ A}$, $R_G=4.7\ \Omega$, $V_{GS}=10\text{ V}$ (see Figure 13)		8.8		ns	
t_r	Rise time		-	18	-	ns	
$t_{d(off)}$	Turn-off delay time				26		ns
t_f	Fall time				4		ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		19	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		76	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 19\text{ A}$, $V_{GS}=0$	-		1.1	V
t_{rr}	Reverse recovery time	$I_{SD} = 19\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD}=25\text{ V}$, $T_j=150\text{ }^\circ\text{C}$		24		ns
Q_{rr}	Reverse recovery charge		-	12		nC
I_{RRM}	Reverse recovery current				1.8	

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

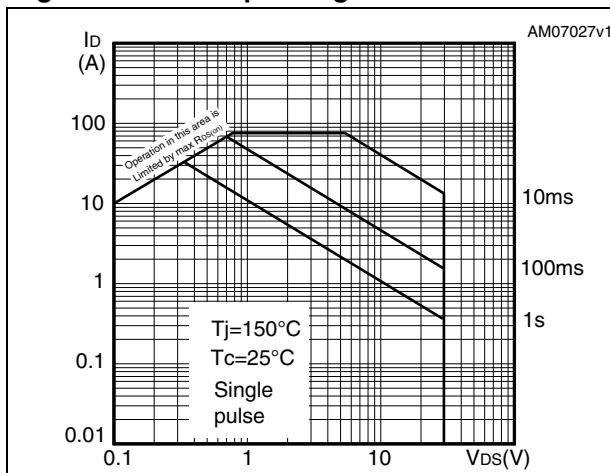


Figure 3. Thermal impedance

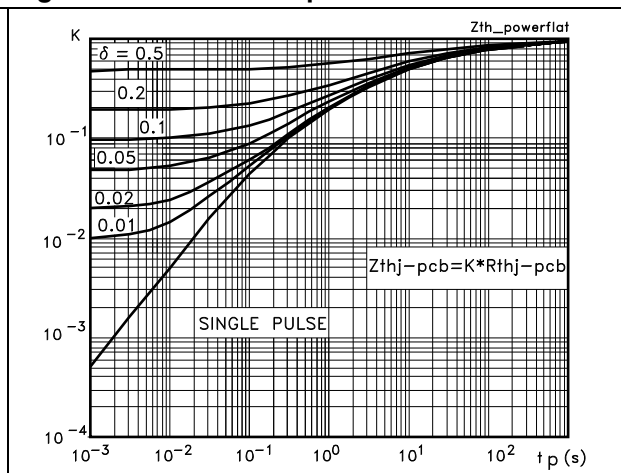


Figure 4. Output characteristics

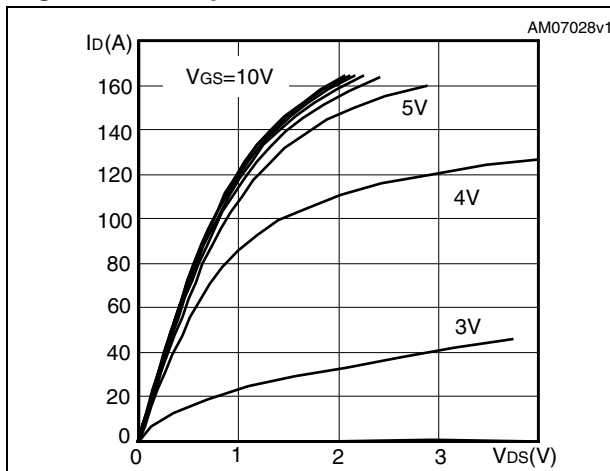


Figure 5. Transfer characteristics

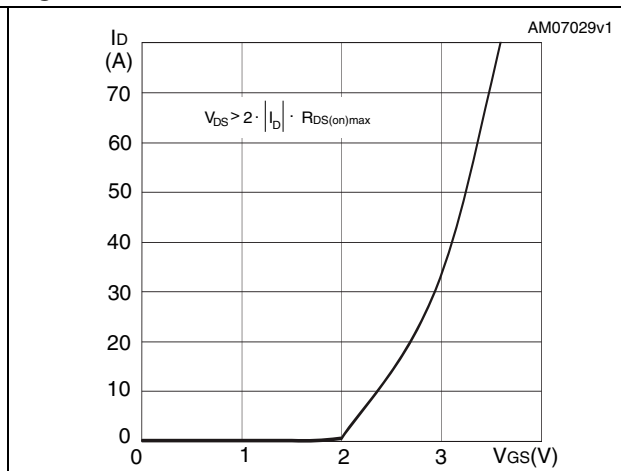


Figure 6. Normalized $B_{V_{DS}}$ vs temperature

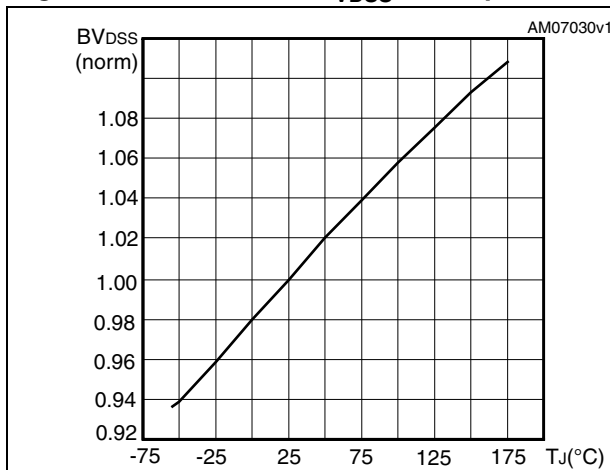


Figure 7. Static drain-source on resistance

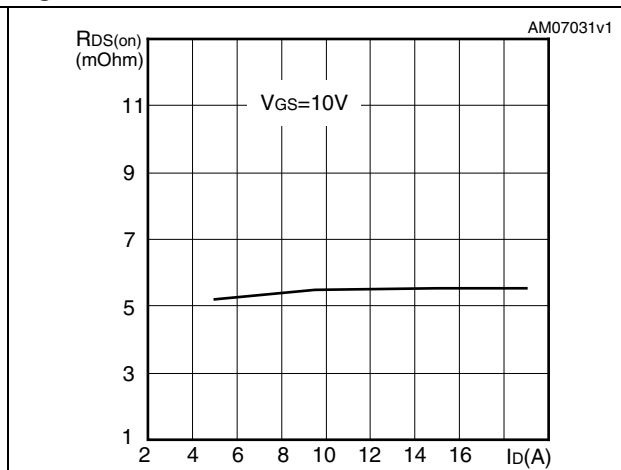


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

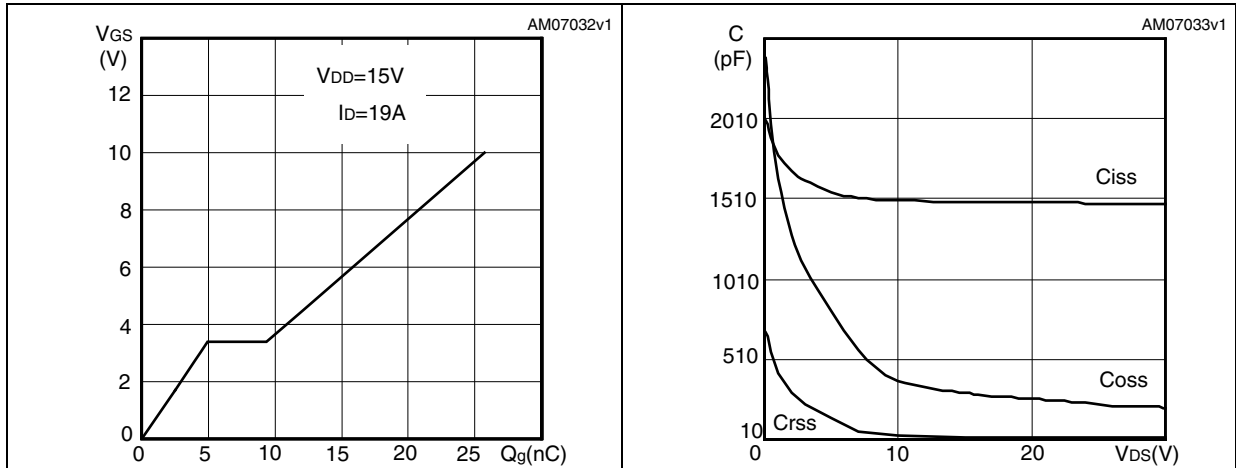


Figure 10. Normalized gate threshold voltage vs temperature Figure 11. Normalized on resistance vs temperature

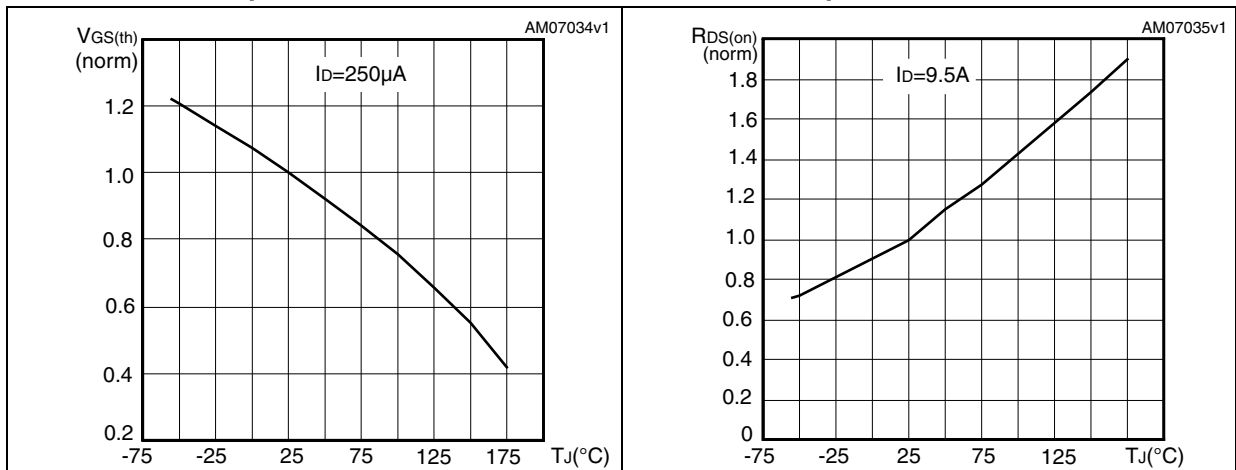
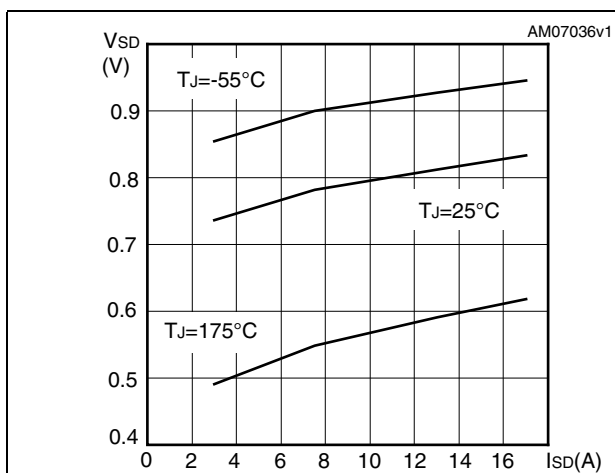


Figure 12. Source-drain diode forward characteristics



3 Test circuits

Figure 13. Switching times test circuit for resistive load

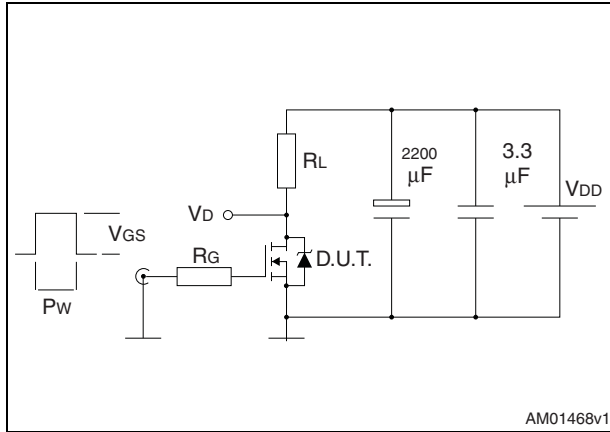


Figure 14. Gate charge test circuit

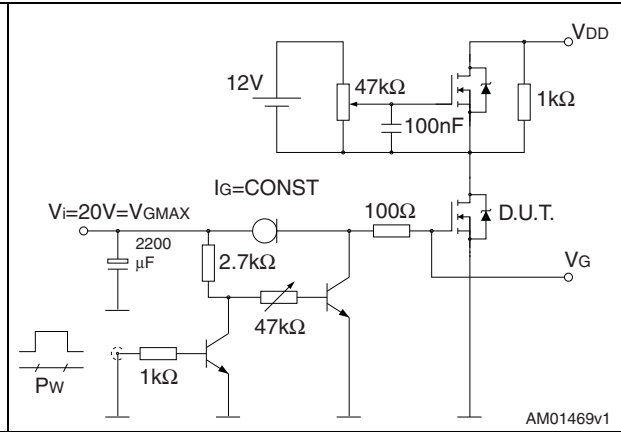


Figure 15. Test circuit for inductive load switching and diode recovery times

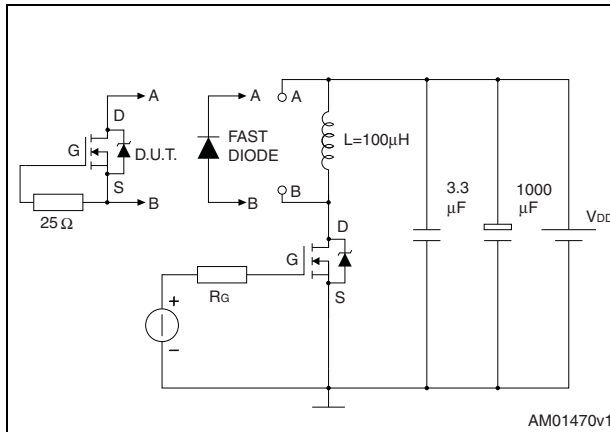


Figure 16. Unclamped inductive load test circuit

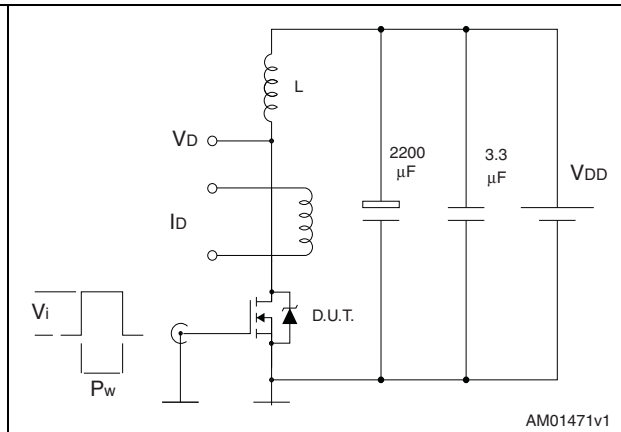


Figure 17. Unclamped inductive waveform

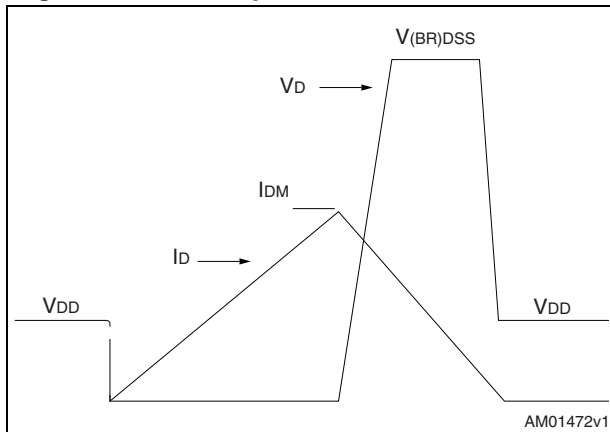
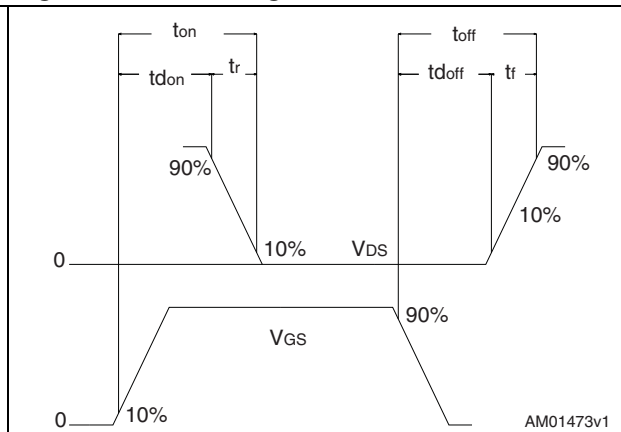


Figure 18. Switching time waveform



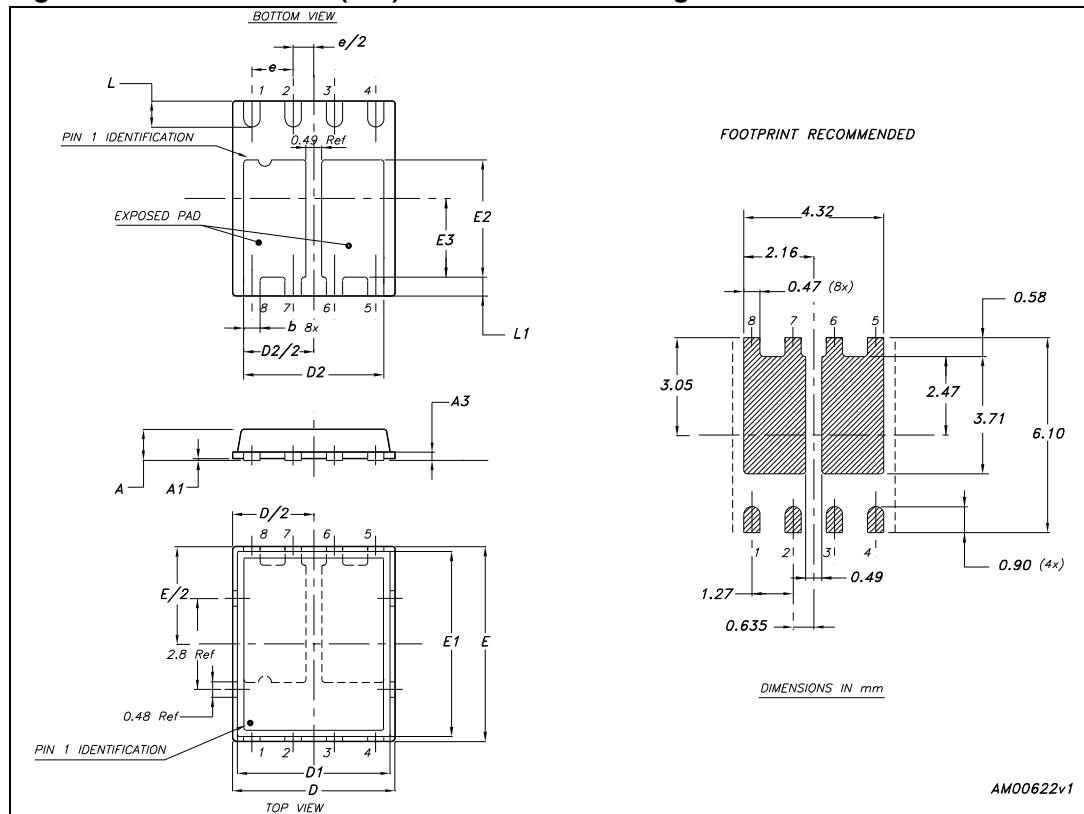
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 9. PowerFLAT™ (5x6) double island mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80	0.83	0.90
A1		0.02	0.05
A3		0.20	
b	0.35	0.40	0.47
D		5.00	
D1		4.75	
D2	4.11	4.21	4.31
E		6.00	
E1		5.75	
E2	3.51	3.61	3.71
E3	2.32	2.42	2.52
e		1.27	
L	0.70	0.80	0.90
L1	0.48	0.58	0.68

Figure 19. PowerFLAT™ (5x6) double island drawing



5 Revision history

Table 10. Document revision history

Date	Revision	Changes
07-Dec-2010	1	First release

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